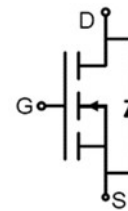


AP7N10K

N-Channel Enhancement Mosfet

Feature

- 100V,7A
 $R_{DS(ON)} < 130m\Omega @ V_{GS}=10V$ TYP:105 m Ω
 $R_{DS(ON)} < 185m\Omega @ V_{GS}=4.5V$ TYP:150 m Ω
- Advanced Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram



Marking and pin Assignment

Application

- PWM applications
- Load Switch
- Power management

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity (PCS) |
|----------------|---------|----------------|-----------|------------|----------------|
| AP7N10K | AP7N10K | TO-252 | 13 inch | - | 2500 |

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|-------------------------------------------------|-----------------|-----------|---------------|
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current ($T_a=25^{\circ}C$) | I_D | 7 | A |
| Continuous Drain Current ($T_a=100^{\circ}C$) | I_D | 4.6 | A |
| Pulsed Drain Current ⁽¹⁾ | I_{DM} | 28 | A |
| Singel Pulsed Avalanche Energy ⁽²⁾ | E_{AS} | 3.2 | mJ |
| Power Dissipation | P_D | 29.4 | W |
| Thermal Resistance from Junction to Case | $R_{\theta JC}$ | 4.25 | $^{\circ}C/W$ |
| Junction Temperature | T_J | 150 | $^{\circ}C$ |
| Storage Temperature | T_{STG} | -55~ +150 | $^{\circ}C$ |

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

| Parameter | Symbol | Test Condition | Min | Type | Max | Unit |
|-------------------------------------------|---------------|-------------------------------------------------------|-----|------|-----------|------------|
| Static Characteristics | | | | | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS} = 0V, I_D = 250\mu A$ | 100 | - | - | V |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = 100V, V_{GS} = 0V$ | - | - | 1 | μA |
| Gate-body leakage current | I_{GSS} | $V_{GS} = \pm 20V, V_{DS} = 0V$ | - | - | ± 100 | nA |
| Gate threshold voltage ⁽³⁾ | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 1 | 1.6 | 2.2 | V |
| Drain-source on-resistance ⁽³⁾ | $R_{DS(on)}$ | $V_{GS} = 10V, I_D = 5A$ | - | 105 | 130 | m Ω |
| | | $V_{GS} = 4.5V, I_D = 3A$ | - | 150 | 185 | |
| Forward tranconductance ⁽³⁾ | g_{FS} | $V_{DS} = 10V, I_D = 5A$ | - | 10 | - | S |
| Dynamic characteristics | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = 50V, V_{GS} = 0V, f = 100kHz$ | - | 212 | - | pF |
| Output Capacitance | C_{oss} | | - | 27.5 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 1.6 | - | |
| Switching characteristics | | | | | | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 50V, I_D = 3A, V_{GS} = 10V, R_G = 2\Omega$ | - | 13.2 | - | ns |
| Turn-on rise time | t_r | | - | 2.2 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 11 | - | |
| Turn-off fall time | t_f | | - | 1.1 | - | |
| Total Gate Charge | Q_g | $V_{DS} = 50V, I_D = 3A, V_{GS} = 10V$ | - | 3.3 | - | nC |
| Gate-Source Charge | Q_{gs} | | - | 0.35 | - | |
| Gate-Drain Charge | Q_{gd} | | - | 0.87 | - | |
| Source-Drain Diode characteristics | | | | | | |
| Diode Forward voltage ⁽³⁾ | V_{DS} | $V_{GS} = 0V, I_S = 1A$ | - | - | 1.2 | V |
| Diode Forward current ⁽⁴⁾ | I_S | | - | - | 7 | A |

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: $T_J = 25^{\circ}\text{C}, V_{DD} = 50V, R_G = 50\Omega, L = 0.5mH$
3. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
4. Surface Mounted on FR4 Board, $t \leq 10$ sec

Test Circuit

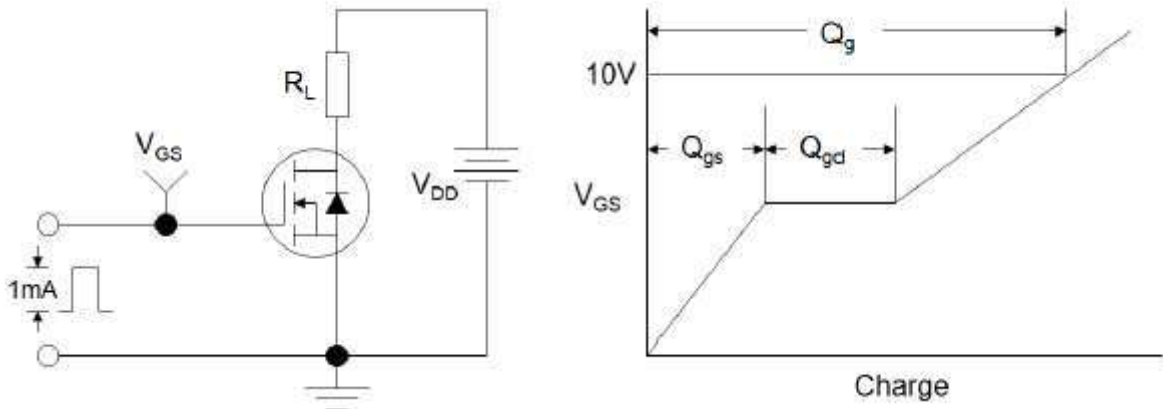


Figure1:Gate Charge Test Circuit & Waveform

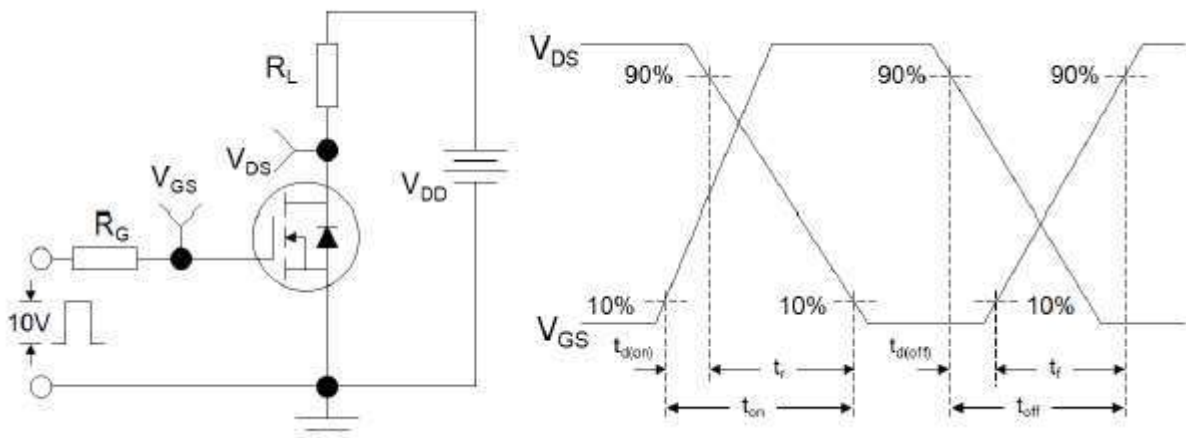


Figure 2: Resistive Switching Test Circuit & Waveforms

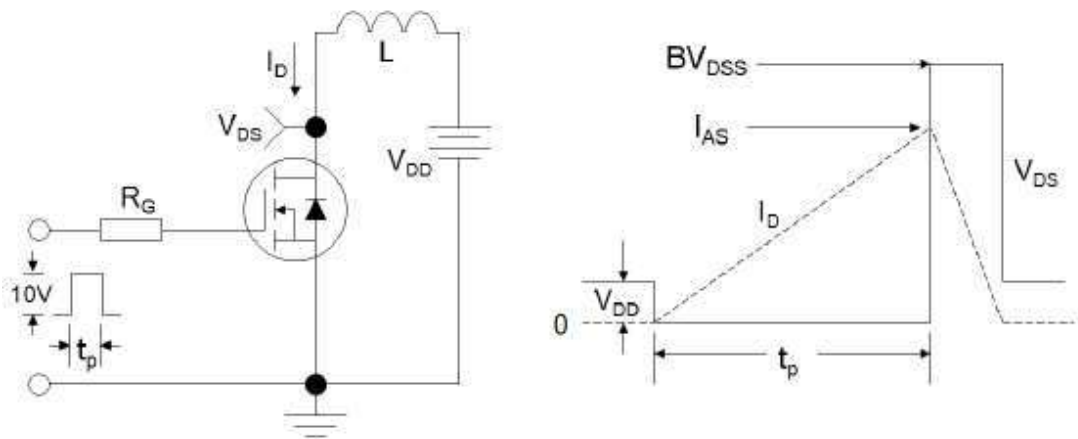


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Typical Performance Characteristics

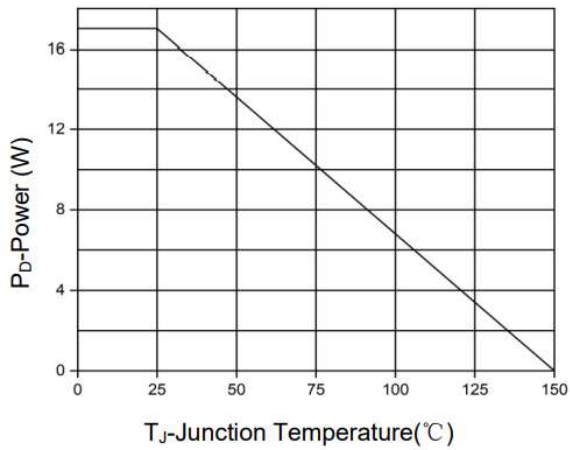


Figure 1. Power Dissipation

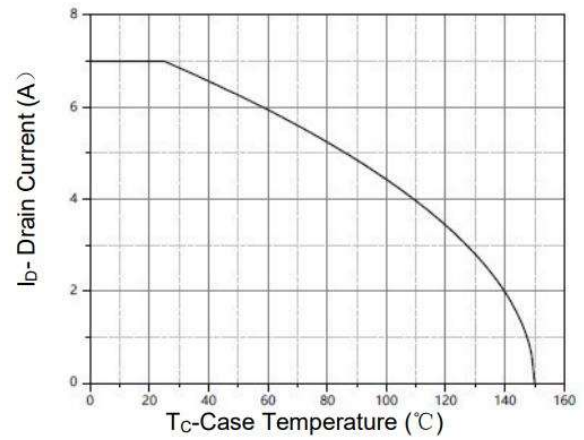


Figure 2. Drain Current

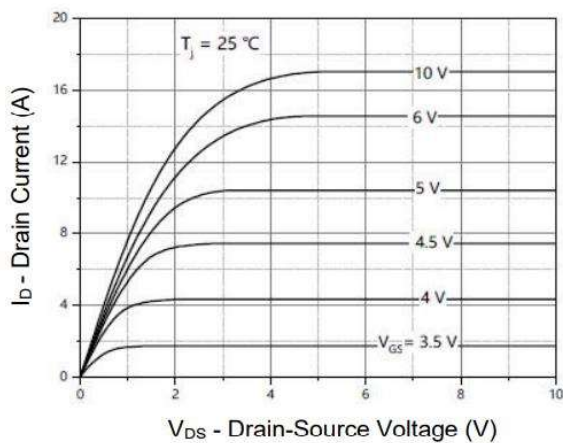


Figure 3. Output characteristics

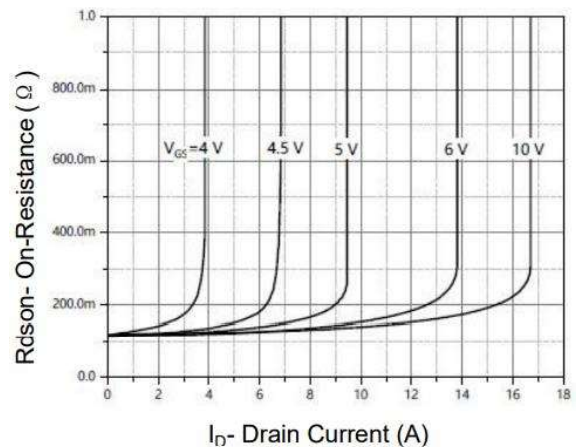


Figure 4. Drain-Source On-state resistance

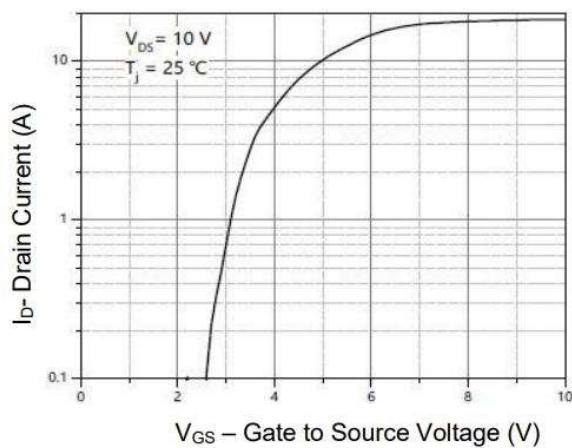


Figure 5. Transfer Characteristics

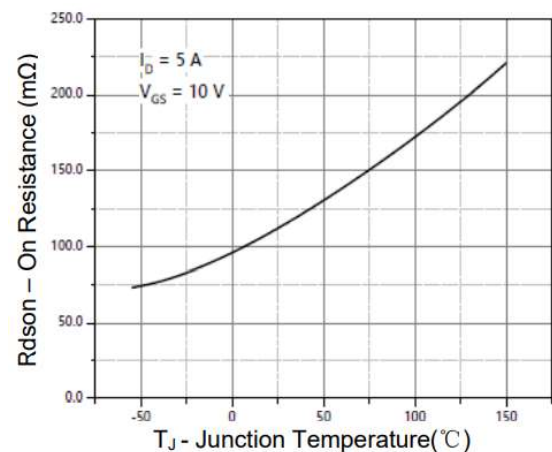


Figure 6. Drain-Source On-State Resistance

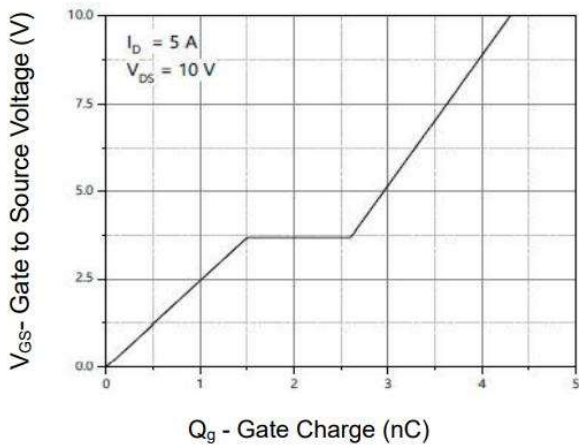


Figure 7. Gate Charge

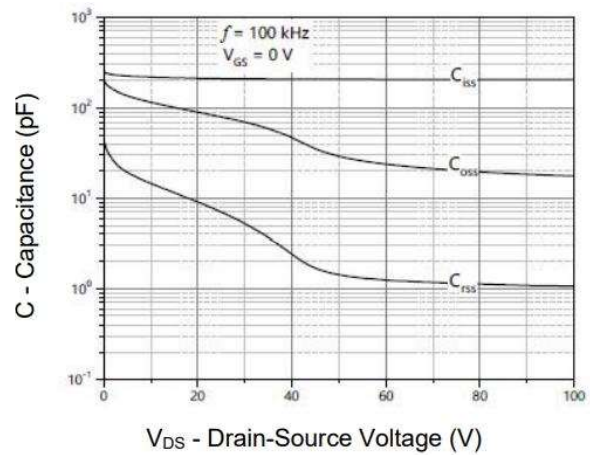


Figure 8. Capacitance vs Vds

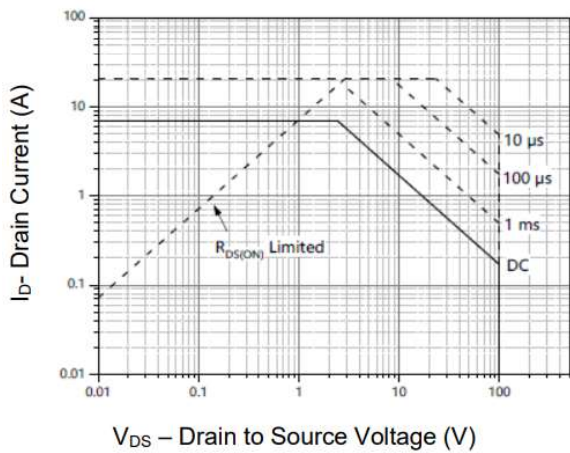


Figure 9. Safe Operation Area

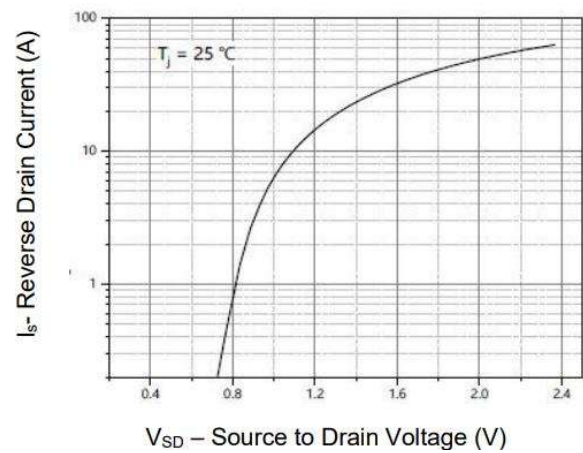


Figure 10. Source- Drain Diode Forward

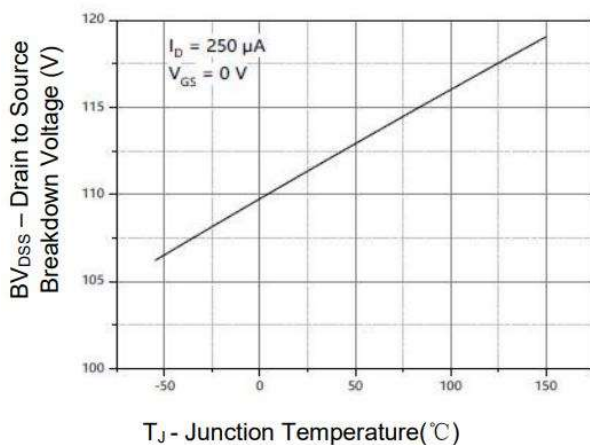
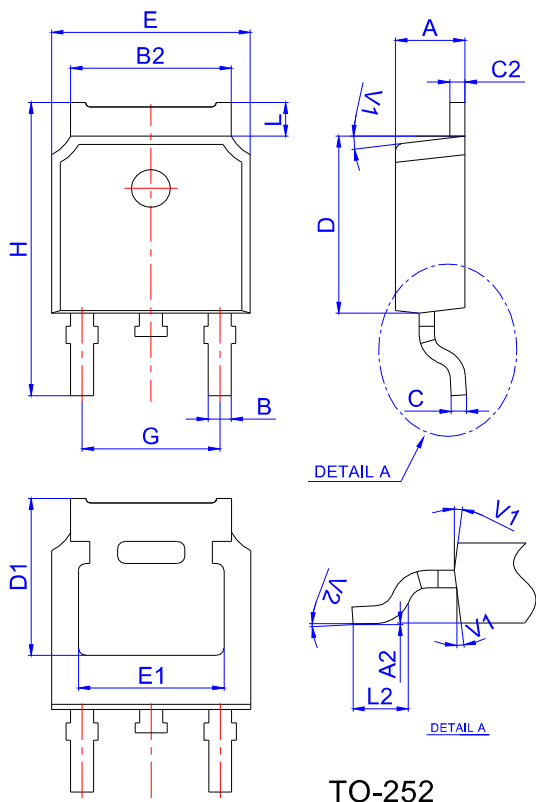


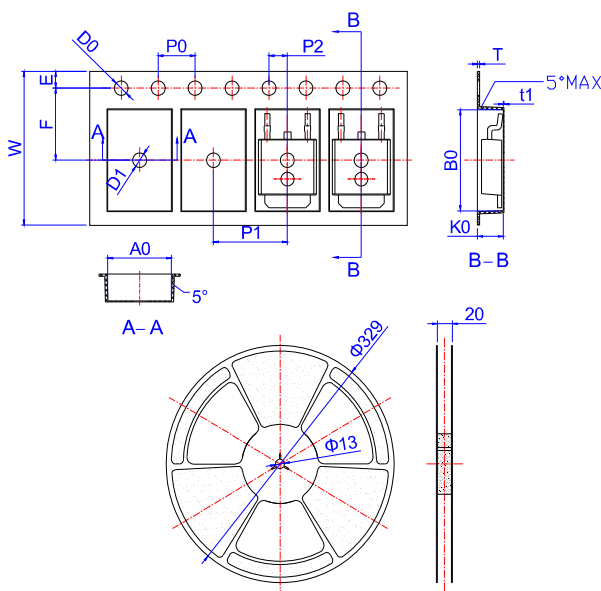
Figure 11. Drain-source breakdown voltage

Package Mechanical Data-TO-252



| Ref. | Dimensions | | | | | |
|------|-------------|------|-------|----------|------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 2.10 | | 2.50 | 0.083 | | 0.098 |
| A2 | 0 | | 0.10 | 0 | | 0.004 |
| B | 0.66 | | 0.86 | 0.026 | | 0.034 |
| B2 | 5.18 | | 5.48 | 0.202 | | 0.216 |
| C | 0.40 | | 0.60 | 0.016 | | 0.024 |
| C2 | 0.44 | | 0.58 | 0.017 | | 0.023 |
| D | 5.90 | | 6.30 | 0.232 | | 0.248 |
| D1 | 5.30REF | | | 0.209REF | | |
| E | 6.40 | | 6.80 | 0.252 | | 0.268 |
| E1 | 4.63 | | | 0.182 | | |
| G | 4.47 | | 4.67 | 0.176 | | 0.184 |
| H | 9.50 | | 10.70 | 0.374 | | 0.421 |
| L | 1.09 | | 1.21 | 0.043 | | 0.048 |
| L2 | 1.35 | | 1.65 | 0.053 | | 0.065 |
| V1 | | 7° | | | 7° | |
| V2 | 0° | | 6° | 0° | | 6° |

Reel Specification-TO-252



| Ref. | Dimensions | | | | | |
|------|-------------|-------|-------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| W | 15.90 | 16.00 | 16.10 | 0.626 | 0.630 | 0.634 |
| E | 1.65 | 1.75 | 1.85 | 0.065 | 0.069 | 0.073 |
| F | 7.40 | 7.50 | 7.60 | 0.291 | 0.295 | 0.299 |
| D0 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 |
| D1 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 |
| P0 | 3.90 | 4.00 | 4.10 | 0.154 | 0.157 | 0.161 |
| P1 | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 |
| P2 | 1.90 | 2.00 | 2.10 | 0.075 | 0.079 | 0.083 |
| A0 | 6.85 | 6.90 | 7.00 | 0.270 | 0.271 | 0.276 |
| B0 | 10.45 | 10.50 | 10.60 | 0.411 | 0.413 | 0.417 |
| K0 | 2.68 | 2.78 | 2.88 | 0.105 | 0.109 | 0.113 |
| T | 0.24 | | 0.27 | 0.009 | | 0.011 |
| t1 | 0.10 | | | 0.004 | | |
| 10P0 | 39.80 | 40.00 | 40.20 | 1.567 | 1.575 | 1.583 |

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